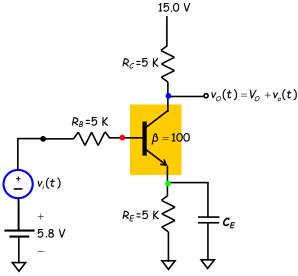
EL213 Analog Circuits Second in-semester exam

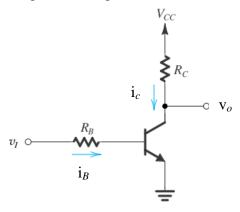
Time: 1:30 Hour Maximum marks: 40

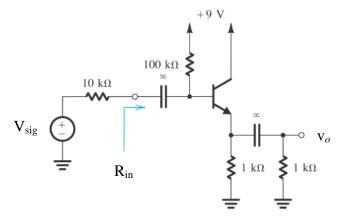
- (a) Make proper assumptions where necessary. (b) Use of calculator is allowed. (c) Each question carries 10 marks. (d) Answer any four questions.
- Q1. Consider the following BJT amplifier



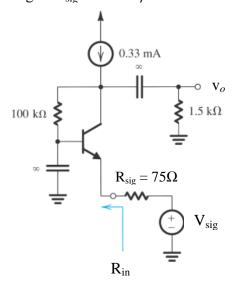
Determine its small-signal, open-circuit voltage gain: $A_o = \frac{v_o(t)}{v_i(t)}$

- Q2. For the emitter-follower circuit shown, the BJT used is specified to have β values in the range of 40 to 200 (a distressing situation for the circuit designer). For the two extreme values of β ($\beta = 40$ and $\beta = 200$), find:
- (a) I_E , V_E , and V_B . (b) the input resistance R_{in} . (c) the voltage gain v_o / v_{sig} .
- Q3. Draw the voltage transfer characteristics for the logic inverter shown below. Compute the breakpoints of the transfer characteristics for a representative case Vcc = 5 V, $R_C = 3 \text{ k}\Omega$, $R_B = 15 \text{ k}\Omega$, $R_C = 45$. Calculate noise margin and the gain in the transition region.





Q4. For the circuit below, find the input resistance R_{in} and the voltage gain v_o/v_{sig} . Assume that the source provides a small signal v_{sig} and that $\beta=100$.



Q5. For a version of the CE amplifier circuit below, R_{sig} = 10 k Ω , R_1 = 68 k Ω , R_2 = 27 k Ω , R_E = 2.2 k Ω , R_C = 4.7 k Ω , and R_L = 10 k Ω . The collector current is 0.8 mA, β = 200, f_T = 1 GHz, and $C\mu$ = 0.8 pF. Neglecting the effect of r_x and r_o , find the midband voltage gain and the upper 3-dB frequency f_H .

